



**Features**

- n Center amplifying gate
- n Metal case with ceramic insulator
- n Low on-state and switching losses

**Typical Applications**

- n AC controllers
- n DC and AC motor control
- n Controlled rectifiers

<b>Part No. Y24KPA-KT19aT</b>			
<b>I<sub>T(AV)</sub></b>	<b>550A</b>		
<b>V<sub>DRM</sub>, V<sub>R</sub>RM</b>	<b>200V</b>	<b>400V</b>	<b>600V</b>

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T <sub>J</sub> (°C)	VALUE			UNIT
					Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled	T <sub>C</sub> =70°C				550	
V <sub>DRM</sub> V <sub>R</sub> RM	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms		125	200		600	V
I <sub>DRM</sub> I <sub>R</sub> RM	Repetitive peak current	at V <sub>DRM</sub> at V <sub>R</sub> RM		125			16	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave		125			8	kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination	V <sub>R</sub> =0.6V <sub>R</sub> RM					320	A <sup>2</sup> s*10 <sup>3</sup>
V <sub>TO</sub>	Threshold voltage			125			0.75	V
r <sub>T</sub>	On-state slope resistance						0.36	mΩ
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =1000A, F=5.0kN		25			1.41	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>		125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> to 800A, Gate pulse t <sub>r</sub> ≤ 0.5μs I <sub>GM</sub> =1.5A		125			100	A/μs
Q <sub>rr</sub>	Recovery charge	I <sub>TM</sub> =1000A, tp=4000μs, di/dt=-20A/μs, V <sub>R</sub> =100V		125		600		μC
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A		25	30		200	mA
V <sub>GT</sub>	Gate trigger voltage				0.8		2.0	V
I <sub>H</sub>	Holding current				20		150	mA
I <sub>L</sub>	Latching current						500	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>		125			0.3	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 5.0kN					0.080	°C/W
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink						0.020	
F <sub>m</sub>	Mounting force				3.3		5.5	kN
T <sub>vj</sub>	Junction temperature				-40		125	°C
T <sub>stg</sub>	Stored temperature				-40		140	°C
W <sub>t</sub>	Weight					60		g
Outline	KT19aT							

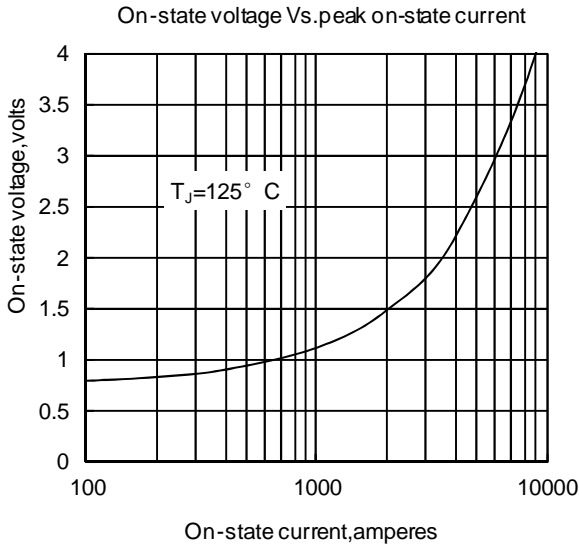


Fig1

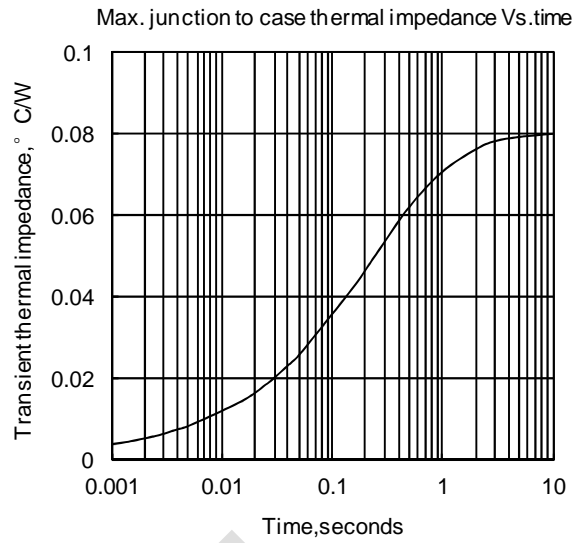


Fig2

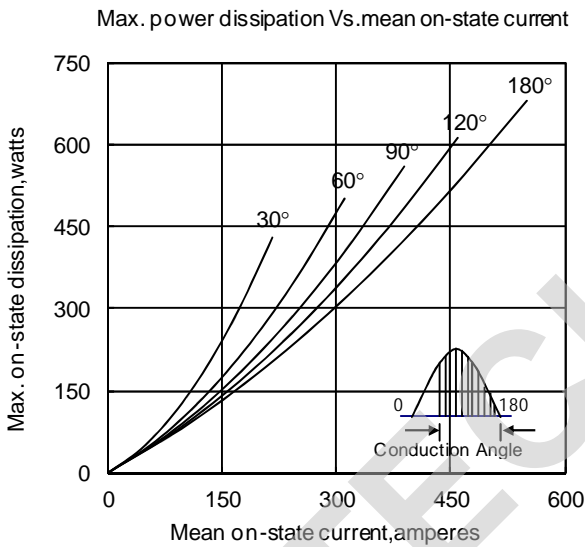


Fig3

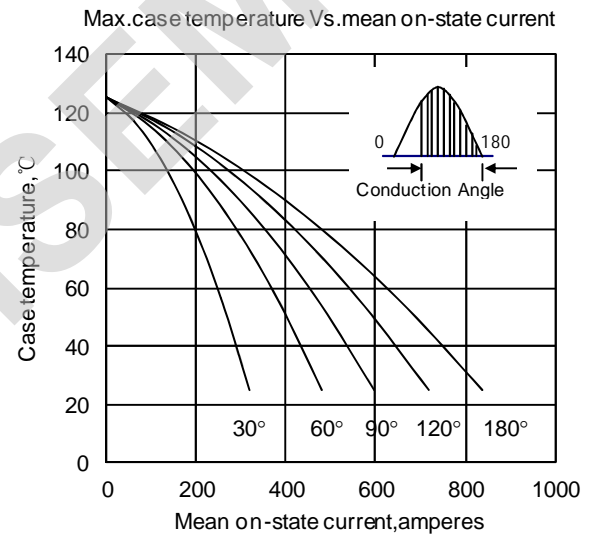


Fig4

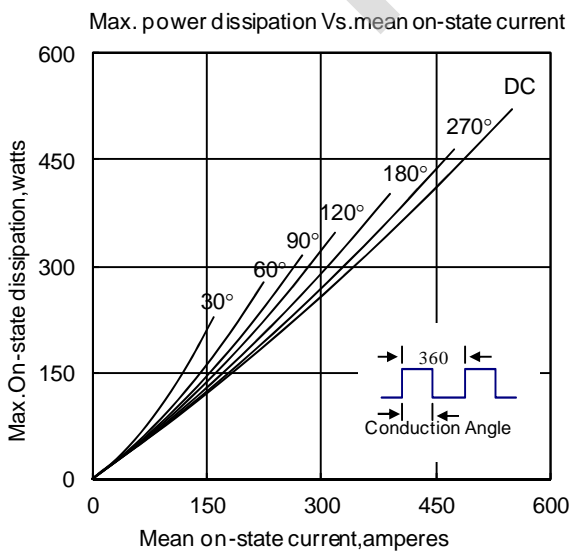


Fig5

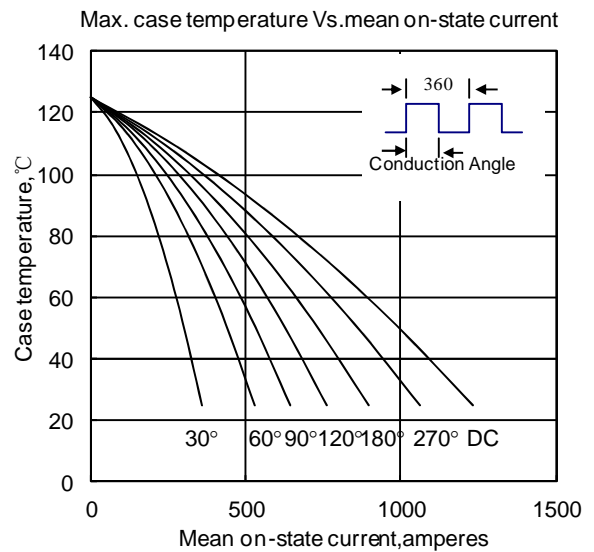


Fig6

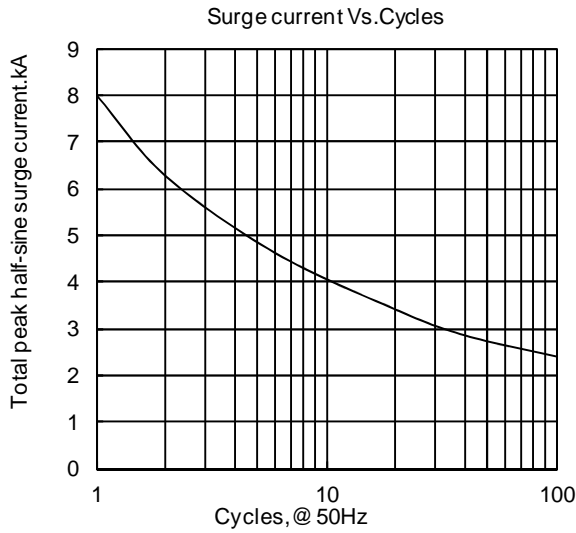


Fig7

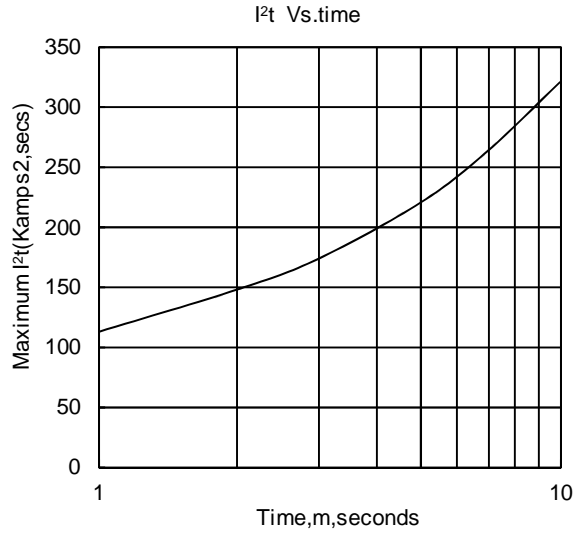


Fig8

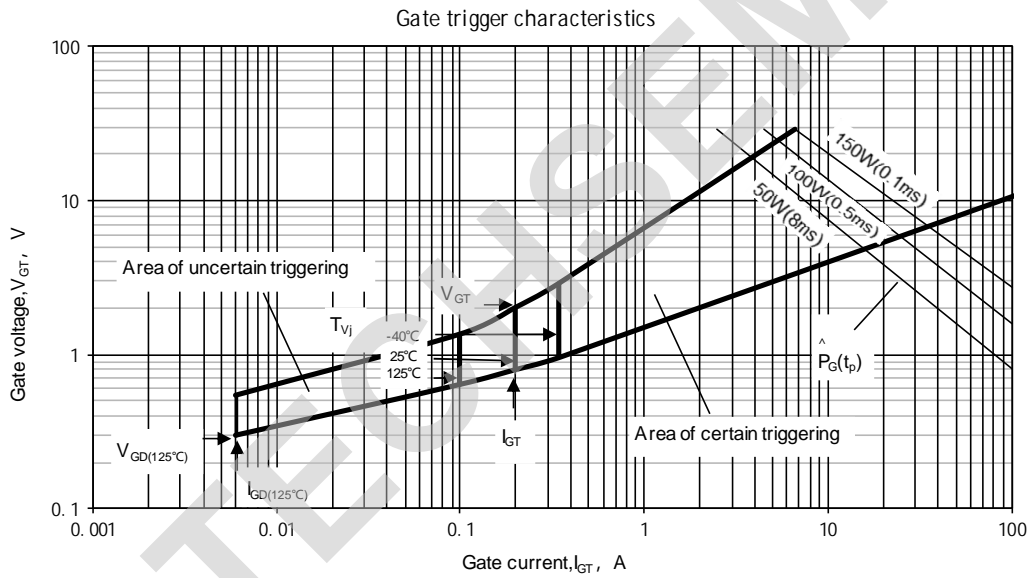
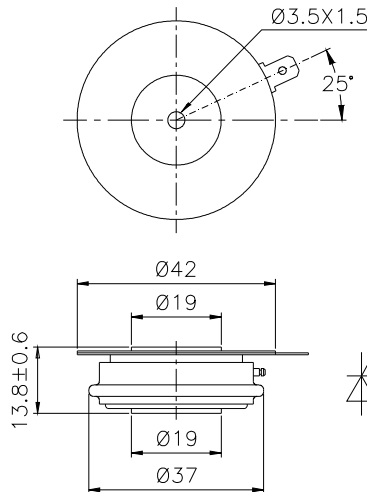


Fig.9

Outline:



TECHSEM reserves the right to change specifications without notice.